Electronic Supplementary Material (ESI) for Journal of Materials Chemistry C. This journal is © The Royal Society of Chemistry 2022

Supporting Information

Preparation of band gap grading Cu₂ZnSn(S,Se)₄ thin film solar cells by the Post-Sulfo-Selenization treatment

Xiang Li, Xinghuan Hu, Hua Liao, Shuai Yang, Xinyu Li, Qiulian Li, Yonggang Zhao, Shurong Wang¹ Key Laboratory of Rural Energy Engineering in Yunnan Province, Yunnan Normal University,

Kunming 650500, PR China

In Supplementary Information, we have provided sample data without bandgap gradient after PSS treatment. It is used to illustrate the degree which the band gap grading effect can improve the performance of thin film solar cell. The sample is named PSS-ng.







Fig.S2 The J-V characteristic of the sample PSS-ng.

¹ Corresponding author. E-mail address: shrw88@aliyun.com (S. Wang).

		1 8			<i>.</i>	
Sample	$V_{oc} (mV)$	J_{sc} (mA/cm ²)	FF (%)	PCE (%)	Rs ($\Omega \cdot cm^2$)	$\mathrm{Rsh}\left(\Omega\cdot\mathrm{cm}^2\right)$
PSS-ng	507.75	32.68	49.59	8.23	3.85	103.5



1

-2.0 -1.8 -1.6 -1.4

Fig.S3 The C-V and $N_{c\mbox{-v}}$ curves of the sample PSS-ng. These data were taken under a 0 to -2 V reverse bias at 300 K.

-0.8 -0.6 -0.4 -0.2 0.0

-1.2 -1.0

Voltage (V)

 10^{17}

0.2

0.3

V_{bias}= 0 V W_d= 0.319 μm

0.4

0.5

Profiling Position (µm)

0.6

0.7

0.8

Table.S1 The parameters of the PSS-ng device.